

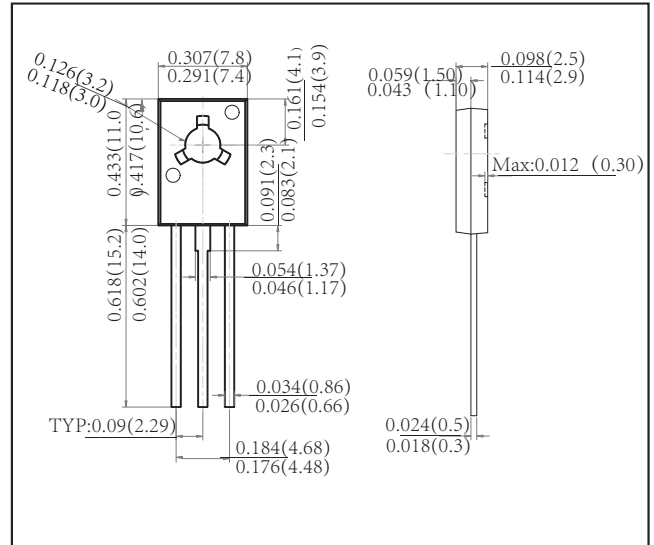
TO-126 Plastic-Encapsulate Transistors

FEATURES

- High Forward Current Transfer Ratio h_{FE} Which has Satisfactory Linearity
- Low Collector-Emitter Saturation Voltage $V_{CE(sat)}$
- TRANSISTOR (NPN)

MECHANICAL DATA

- Case style:TO-126 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

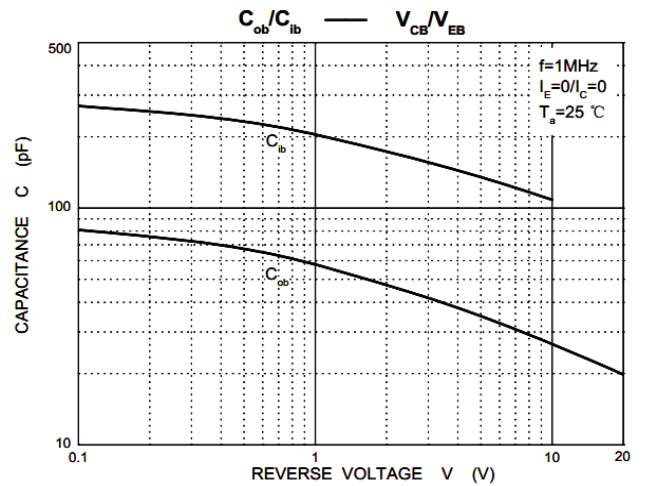
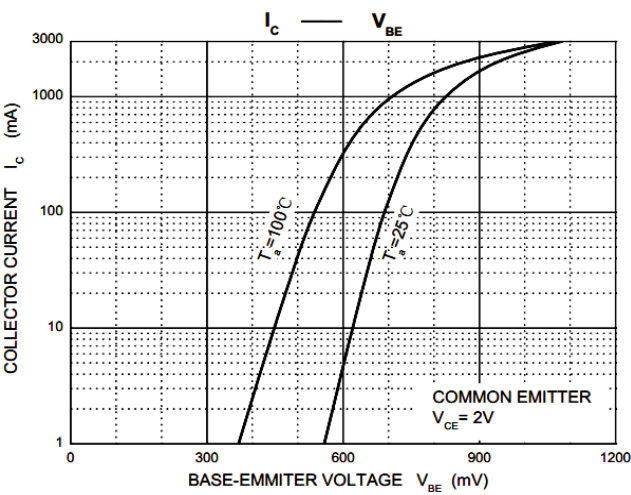
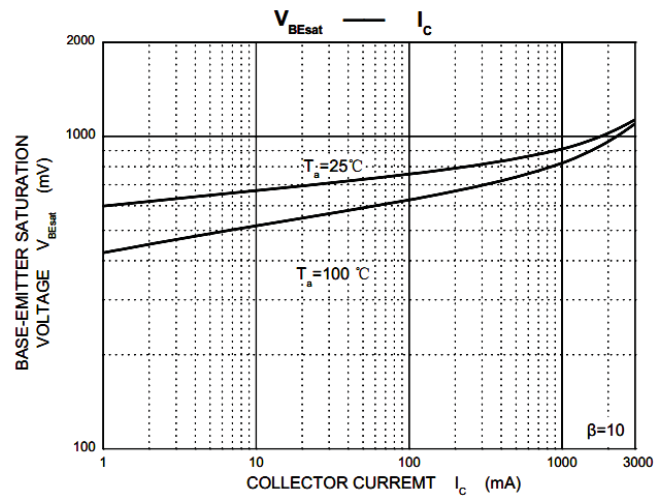
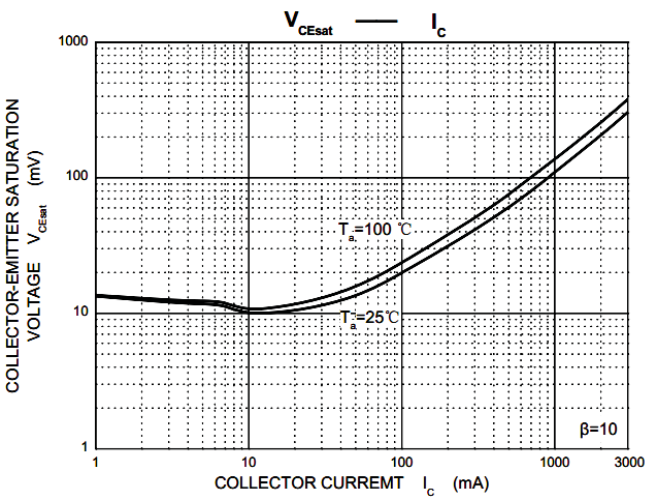
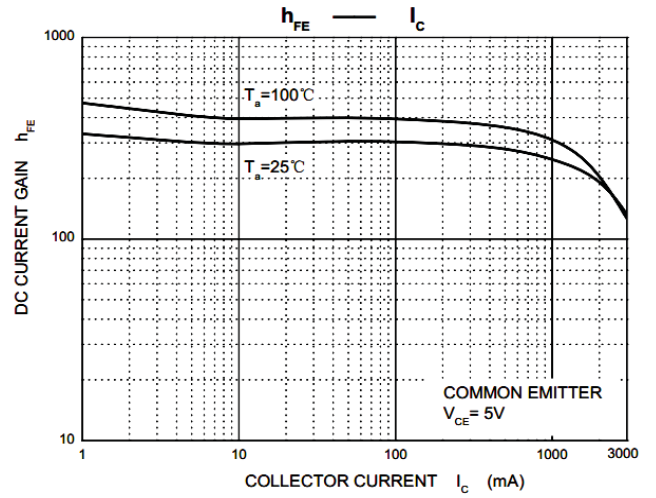
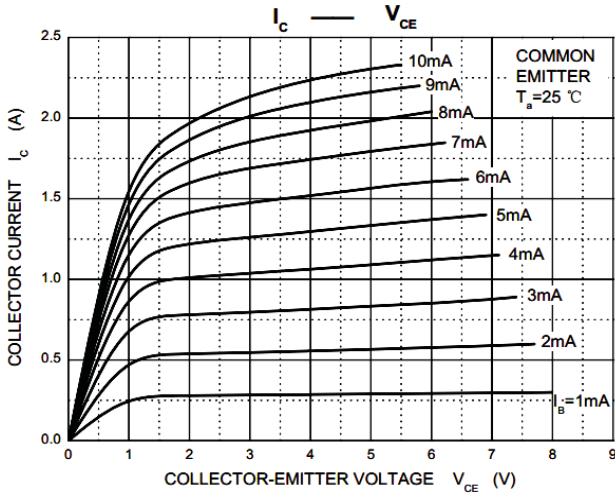
@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	40	V
Collector Emitter Voltage	V_{CEO}	30	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current -Continuous	I_C	3	A
Collector Power Dissipation	P_C	1.25	W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 ~ +150	°C

MOSFET ELECTRICAL CHARACTERISTICS $T_A=25^\circ C$ unless otherwise specified

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10\ 0\ \mu A, I_E = 0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10\ mA, I_B = 0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100\ \mu A, I_C = 0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB} = 40\ V, I_E = 0$			1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = 30\ V, I_B = 0$			10	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 6\ V, I_C = 0$			1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 5\ V, I_C = 1mA$	200		400	
	$h_{FE(2)}$	$V_{CE} = 2\ V, I_C = 1\ A$	60			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 2\ A, I_B = 0.2A$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 2\ A, I_B = 0.2A$			1.5	V
Transition frequency	f_T	$V_{CE} = 5\ V, I_C = 0.1\ A, f = 10\ MHz$		90		MHz

RATINGS AND CHARACTERISTIC CURVES



RATINGS AND CHARACTERISTIC CURVES

